List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/2921382/publications.pdf Version: 2024-02-01



TILDEL CHEN

#	Article	IF	CITATIONS
1	Nanofabrication by scanning probe microscope lithography: A review. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 877.	1.6	404
2	Nonâ€Volatile Organic Memory Applications Enabled by In Situ Synthesis of Gold Nanoparticles in a Selfâ€Assembled Block Copolymer. Advanced Materials, 2008, 20, 2325-2331.	21.0	186
3	Associative memory realized by a reconfigurable memristive Hopfield neural network. Nature Communications, 2015, 6, 7522.	12.8	182
4	Hexagonal Boron Nitride Thin Film for Flexible Resistive Memory Applications. Advanced Functional Materials, 2016, 26, 2176-2184.	14.9	167
5	A light-stimulated synaptic transistor with synaptic plasticity and memory functions based on InGaZnOx–Al2O3 thin film structure. Journal of Applied Physics, 2016, 119, .	2.5	153
6	3D hierarchical Co ₃ O ₄ @Co ₃ S ₄ nanoarrays as cathode materials for asymmetric pseudocapacitors. Journal of Materials Chemistry A, 2016, 4, 3287-3296.	10.3	147
7	Charging phenomena in pentacene-gold nanoparticle memory device. Applied Physics Letters, 2007, 90, 042906.	3.3	141
8	Bond-orderÂbond-lengthÂbond-strength (bond-OLS) correlation mechanism for the shape-and-size dependence of a nanosolid. Journal of Physics Condensed Matter, 2002, 14, 7781-7795.	1.8	125
9	Emulating the paired-pulse facilitation of a biological synapse with a NiOx-based memristor. Applied Physics Letters, 2013, 102, .	3.3	119
10	Thickness effect on the band gap and optical properties of germanium thin films. Journal of Applied Physics, 2010, 107, .	2.5	117
11	3D hierarchical defect-rich NiMo3S4 nanosheet arrays grown on carbon textiles for high-performance sodium-ion batteries and hydrogen evolution reaction. Nano Energy, 2018, 49, 460-470.	16.0	107
12	Ultrahigh Performance of Novel Capacitive Deionization Electrodes based on A Three-Dimensional Graphene Architecture with Nanopores. Scientific Reports, 2016, 6, 18966.	3.3	105
13	Bifunctional porous iron phosphide/carbon nanostructure enabled high-performance sodium-ion battery and hydrogen evolution reaction. Energy Storage Materials, 2018, 15, 98-107.	18.0	102
14	Optical properties of silicon nanocrystals embedded in aSiO2matrix. Physical Review B, 2005, 72, .	3.2	99
15	Micellar poly(styrene-b-4-vinylpyridine)-nanoparticle hybrid system for non-volatile organic transistor memory. Journal of Materials Chemistry, 2009, 19, 7354.	6.7	99
16	Low energy consumption dual-ion electrochemical deionization system using NaTi2(PO4)3-AgNPs electrodes. Desalination, 2019, 451, 241-247.	8.2	99
17	Fabrication of n-ZnO:Alâ^•p-SiC(4H) heterojunction light-emitting diodes by filtered cathodic vacuum arc technique. Applied Physics Letters, 2005, 86, 241111.	3.3	97
18	A Deformable and Highly Robust Ethyl Cellulose Transparent Conductor with a Scalable Silver Nanowires Bundle Micromesh. Advanced Materials, 2018, 30, e1802803.	21.0	95

#	Article	IF	CITATIONS
19	Emulating the Ebbinghaus forgetting curve of the human brain with a NiO-based memristor. Applied Physics Letters, 2013, 103, .	3.3	90
20	Two dimensional layered Co _{0.85} Se nanosheets as a high-capacity anode for lithium-ion batteries. Nanoscale, 2016, 8, 14992-15000.	5.6	90
21	Ultraviolet and visible electroluminescence from n-ZnOâ^•SiOxâ^•(n,p)-Si heterostructured light-emitting diodes. Applied Physics Letters, 2008, 93, .	3.3	88
22	Direct Observation of Indium Conductive Filaments in Transparent, Flexible, and Transferable Resistive Switching Memory. ACS Nano, 2017, 11, 1712-1718.	14.6	83
23	Surface modification of Na ₂ Ti ₃ O ₇ nanofibre arrays using N-doped graphene quantum dots as advanced anodes for sodium-ion batteries with ultra-stable and high-rate capability. Journal of Materials Chemistry A, 2019, 7, 12751-12762.	10.3	83
24	An extended `quantum confinement' theory: surface-coordination imperfection modifies the entire band structure of a nanosolid. Journal Physics D: Applied Physics, 2001, 34, 3470-3479.	2.8	82
25	Synthesis and Electrical Transport of Novel Channel-StructuredÎ ² -AgVO3. Small, 2007, 3, 1174-1177.	10.0	82
26	Direct Observation of Conducting Filaments in Tungsten Oxide Based Transparent Resistive Switching Memory. ACS Applied Materials & Interfaces, 2016, 8, 27885-27891.	8.0	80
27	Recent Developments in Tip-Based Nanofabrication and Its Roadmap. Journal of Nanoscience and Nanotechnology, 2008, 8, 2167-2186.	0.9	76
28	Review of Nanostructured Resistive Switching Memristor and Its Applications. Nanoscience and Nanotechnology Letters, 2014, 6, 729-757.	0.4	76
29	Refractive indices of textured indium tin oxide and zinc oxide thin films. Thin Solid Films, 2006, 510, 95-101.	1.8	74
30	Multiferroic properties of sputtered BiFeO3 thin films. Applied Physics Letters, 2008, 92, .	3.3	67
31	Nitrogen-enhanced negative bias temperature instability: An insight by experiment and first-principle calculations. Applied Physics Letters, 2003, 82, 1881-1883.	3.3	66
32	A study on Si nanocrystal formation in Si-implanted SiO2films by x-ray photoelectron spectroscopy. Journal Physics D: Applied Physics, 2003, 36, L97-L100.	2.8	66
33	Evolution of Si suboxides into Si nanocrystals during rapid thermal annealing as revealed by XPS and Raman studies. Journal of Crystal Growth, 2009, 311, 1296-1301.	1.5	61
34	Novel concepts in functional resistive switching memories. Journal of Materials Chemistry C, 2016, 4, 9637-9645.	5.5	59
35	A simple technique to determine barrier height change in gate oxide caused by electrical stress. IEEE Transactions on Electron Devices, 2002, 49, 1493-1496.	3.0	54
36	Synaptic long-term potentiation realized in Pavlov's dog model based on a NiOx-based memristor. Journal of Applied Physics, 2014, 116, .	2.5	52

#	Article	IF	CITATIONS
37	Hydrothermally synthesized graphene and Fe ₃ O ₄ nanocomposites for high performance capacitive deionization. RSC Advances, 2016, 6, 11967-11972.	3.6	52
38	Dielectric functions of Si nanocrystals embedded in aSiO2matrix. Physical Review B, 2003, 68, .	3.2	49
39	Memory characteristics of MOSFETs with densely stacked silicon nanocrystal Layers in the gate oxide synthesized by low-energy ion beam. IEEE Electron Device Letters, 2006, 27, 231-233.	3.9	47
40	Visualizing charge transport in silicon nanocrystals embedded in SiO2 films with electrostatic force microscopy. Applied Physics Letters, 2004, 85, 2941-2943.	3.3	45
41	Microstructure of Magnetron Sputtered Amorphous SiO <i>_x</i> Films: Formation of Amorphous Si Coreâ°Shell Nanoclusters. Journal of Physical Chemistry C, 2010, 114, 2414-2420.	3.1	45
42	Photoluminescence of Si Nanosolids near the Lower End of the Size Limit. Journal of Physical Chemistry B, 2002, 106, 11725-11727.	2.6	43
43	Upper limit of blue shift in the photoluminescence of CdSe and CdS nanosolids. Acta Materialia, 2002, 50, 4687-4693.	7.9	43
44	Recent developments on microablation of glass materials using excimer lasers. Optics and Lasers in Engineering, 2007, 45, 975-992.	3.8	41
45	Dielectric suppression of nanosolid silicon. Nanotechnology, 2004, 15, 1802-1806.	2.6	40
46	High-Temperature Lasing Characteristics of ZnO Epilayers. Advanced Materials, 2006, 18, 771-774.	21.0	40
47	Influence of nanocrystal size on optical properties of Si nanocrystals embedded in SiO2 synthesized by Si ion implantation. Journal of Applied Physics, 2007, 101, 103525.	2.5	40
48	Relationship between interfacial nitrogen concentration and activation energies of fixed-charge trapping and interface state generation under bias-temperature stress condition. Applied Physics Letters, 2003, 82, 269-271.	3.3	39
49	Predicting House Price With a Memristor-Based Artificial Neural Network. IEEE Access, 2018, 6, 16523-16528.	4.2	39
50	Resistive switching in aluminum/anodized aluminum film structure without forming process. Journal of Applied Physics, 2009, 106, .	2.5	38
51	Length, Strength, Extensibility, and Thermal Stability of a Auâ^'Au Bond in the Gold Monatomic Chain. Journal of Physical Chemistry B, 2004, 108, 2162-2167.	2.6	37
52	Highly spectrum-selective ultraviolet photodetector based on p-NiO/n-IGZO thin film heterojunction structure. Optics Express, 2015, 23, 27683.	3.4	37
53	Strong violet and green-yellow electroluminescence from silicon nitride thin films multiply implanted with Si ions. Applied Physics Letters, 2009, 94, .	3.3	35
54	Conduction mechanisms at low- and high-resistance states in aluminum/anodic aluminum oxide/aluminum thin film structure. Journal of Applied Physics, 2012, 112, .	2.5	35

#	Article	IF	CITATIONS
55	Effects of free electrons and quantum confinement in ultrathin ZnO films: a comparison between undoped and Al-doped ZnO. Optics Express, 2013, 21, 14131.	3.4	35
56	Mechanism of nitrogen-enhanced negative bias temperature instability in pMOSFET. Microelectronics Reliability, 2005, 45, 19-30.	1.7	34
57	Handwritten-Digit Recognition by Hybrid Convolutional Neural Network based on HfO2 Memristive Spiking-Neuron. Scientific Reports, 2018, 8, 12546.	3.3	34
58	Impact of programming mechanisms on the performance and reliability of nonvolatile memory devices based on Si nanocrystals. IEEE Transactions on Electron Devices, 2006, 53, 663-667.	3.0	33
59	Interface trap generation by FN injection under dynamic oxide field stress. IEEE Transactions on Electron Devices, 1998, 45, 1920-1926.	3.0	32
60	Influence of localized surface plasmon resonance and free electrons on the optical properties of ultrathin Au films: a study of the aggregation effect. Optics Express, 2014, 22, 5124.	3.4	32
61	Current transport and its effect on the determination of the Schottky-barrier height in a typical system: Gold on silicon. Solid-State Electronics, 1993, 36, 949-954.	1.4	31
62	Core-Level Shift of Si Nanocrystals Embedded in a SiO2Matrix. Journal of Physical Chemistry B, 2004, 108, 16609-16612.	2.6	30
63	Static dielectric constant of isolated silicon nanocrystals embedded in a SiO2 thin film. Applied Physics Letters, 2006, 88, 063103.	3.3	30
64	WS ₂ –3D graphene nano-architecture networks for high performance anode materials of lithium ion batteries. RSC Advances, 2016, 6, 107768-107775.	3.6	29
65	Electrical properties of TaN–Cu nanocomposite thin films. Ceramics International, 2004, 30, 1879-1883.	4.8	28
66	Charging effect on current conduction in aluminum nitride thin films containing Al nanocrystals. Applied Physics Letters, 2006, 89, 123101.	3.3	28
67	Analytical reaction-diffusion model and the modeling of nitrogen-enhanced negative bias temperature instability. Applied Physics Letters, 2006, 88, 172109.	3.3	28
68	Scratch properties of nickel thin films using atomic force microscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 202-210.	1.2	28
69	Electrically tunable white-color electroluminescence from Si-implanted silicon nitride thin film. Optics Express, 2010, 18, 20439.	3.4	28
70	Effect of Exposure to Ultraviolet-Activated Oxygen on the Electrical Characteristics of Amorphous Indium Gallium Zinc Oxide Thin Film Transistors. ECS Solid State Letters, 2013, 2, Q21-Q24.	1.4	28
71	A study on the evolution of dielectric function of ZnO thin films with decreasing film thickness. Journal of Applied Physics, 2014, 115, .	2.5	27
72	Charging Effect on Electrical Characteristics of MOS Structures with Si Nanocrystal Distribution in Gate Oxide. Electrochemical and Solid-State Letters, 2004, 7, G134.	2.2	26

#	Article	IF	CITATIONS
73	Memory effect of Al-rich AlN films synthesized with rf magnetron sputtering. Applied Physics Letters, 2005, 87, 033112.	3.3	26
74	Unlocking the potential of SnS2: Transition metal catalyzed utilization of reversible conversion and alloying reactions. Scientific Reports, 2017, 7, 41015.	3.3	26
75	Temperature dependence of the ideality factor of GaAs and Si schottky diodes. Physica Status Solidi A, 1995, 152, 563-571.	1.7	25
76	Negative Bias Temperature Instability on Plasma-Nitrided Silicon Dioxide Film. Japanese Journal of Applied Physics, 2002, 41, L314-L316.	1.5	25
77	Discriminating Crystal Binding from the Atomic Trapping of a Core Electron at Energy Levels Shifted by Surface Relaxation or Nanosolid Formation. Journal of Physical Chemistry B, 2003, 107, 411-414.	2.6	25
78	Thermal annealing effect on the band gap and dielectric functions of silicon nanocrystals embedded in SiO2 matrix. Applied Physics Letters, 2005, 87, 121903.	3.3	25
79	Room temperature deposition of p-type arsenic doped ZnO polycrystalline films by laser-assist filtered cathodic vacuum arc technique. Journal of Applied Physics, 2007, 101, 094905.	2.5	25
80	Effect of annealing on charge transfer in Ge nanocrystal based nonvolatile memory structure. Journal of Applied Physics, 2009, 106, .	2.5	24
81	Split of surface plasmon resonance of gold nanoparticles on silicon substrate: a study of dielectric functions. Optics Express, 2010, 18, 21926.	3.4	24
82	Snapback behavior of the postbreakdown I–V characteristics in ultrathin SiO2 films. Applied Physics Letters, 2001, 78, 492-494.	3.3	23
83	Influence of charge trapping on electroluminescence from Si-nanocrystal light emitting structure. Journal of Applied Physics, 2007, 101, 104306.	2.5	23
84	Amorphousâ€ S iâ€Based Resistive Switching Memories with Highly Reduced Electroforming Voltage and Enlarged Memory Window. Advanced Electronic Materials, 2016, 2, 1500370.	5.1	23
85	Linear relationship between H+-trapping reaction energy and defect generation: Insight into nitrogen-enhanced negative bias temperature instability. Applied Physics Letters, 2003, 83, 530-532.	3.3	22
86	Modeling of a selective solar absorber thin film structure based on double TiNxOy layers for concentrated solar power applications. Solar Energy, 2017, 142, 33-38.	6.1	21
87	Atomic Modeling of Nitrogen Neighboring Effect on Negative Bias Temperature Instability of pMOSFETs. IEEE Electron Device Letters, 2004, 25, 504-506.	3.9	20
88	Charging dynamics of discrete gold nanoparticle arrays self-assembled within a poly(styrene-b-4-vinylpyridine) diblock copolymer template. Applied Physics Letters, 2008, 93, 222908.	3.3	20
89	Evolution of dielectric function of Al-doped ZnO thin films with thermal annealing: effect of band gap expansion and free-electron absorption. Optics Express, 2014, 22, 23086.	3.4	20
90	Investigation of localized surface plasmon resonance of TiN nanoparticles in TiN_xO_y thin films. Optical Materials Express, 2016, 6, 2422.	3.0	20

#	Article	IF	CITATIONS
91	Smart electronic skin having gesture recognition function by LSTM neural network. Applied Physics Letters, 2018, 113, .	3.3	20
92	Interface chemistry and band bending induced by Pt deposition onto GaP(110). Surface Science, 1991, 251-252, 472-477.	1.9	19
93	The influence of the implantation dose and energy on the electroluminescence of Si ⁺ -implanted amorphous SiO ₂ thin films. Nanotechnology, 2007, 18, 455306.	2.6	19
94	Effect of O2 plasma immersion on electrical properties and transistor performance of indium gallium zinc oxide thin films. Thin Solid Films, 2013, 545, 533-536.	1.8	19
95	STBNN: Hardware-friendly spatio-temporal binary neural network with high pattern recognition accuracy. Neurocomputing, 2020, 409, 351-360.	5.9	19
96	The interaction of platinum with GaP(110): band bending and surface photovoltage effects. Applied Surface Science, 1992, 56-58, 233-241.	6.1	18
97	Depth profiling of Si nanocrystals in Si-implanted SiO2 films by spectroscopic ellipsometry. Applied Physics Letters, 2002, 81, 4724-4726.	3.3	18
98	Influence of silicon-nanocrystal distribution in SiO2 matrix on charge injection and charge decay. Applied Physics Letters, 2005, 86, 152110.	3.3	18
99	Fabrication of thin-film organic transistor on flexible substrate via ultraviolet transfer embossing. Applied Physics Letters, 2007, 90, 243502.	3.3	18
100	Bottom-contact poly(3,3‴-didodecylquaterthiophene) thin-film transistors with reduced contact resistance. Organic Electronics, 2008, 9, 14-20.	2.6	18
101	Influence of oxygen partial pressure on magnetron sputtered Sr0.8Nd0.3Bi2.5Ta2O9+x ferroelectric thin films. Journal of Alloys and Compounds, 2008, 457, 549-554.	5.5	18
102	Annealing effect on the optical properties of implanted silicon in a silicon nitride matrix. Applied Physics Letters, 2008, 93, .	3.3	18
103	Electroluminescence of as-sputtered silicon-rich SiOx films. Vacuum, 2010, 84, 1043-1048.	3.5	18
104	A Neuromorphic-Hardware Oriented Bio-Plausible Online-Learning Spiking Neural Network Model. IEEE Access, 2019, 7, 71730-71740.	4.2	18
105	Influence of nitrogen on tunneling barrier heights and effective masses of electrons and holes at lightly-nitrided SiO2â^•Si interface. Journal of Applied Physics, 2004, 96, 5912-5914.	2.5	17
106	Effects of annealing on the microstructure and electrical properties of TaN-Cu nanocomposite thin films. Surface and Coatings Technology, 2005, 193, 173-177.	4.8	17
107	Charging-Induced Changes in Reverse Current–Voltage Characteristics of Al/Al-Rich \$hbox{Al}_{2}hbox{O}_{3}/hbox{p-Si}\$ Diodes. IEEE Transactions on Electron Devices, 2009, 56, 2060-2064.	3.0	17
108	Laterally-current-injected light-emitting diodes based on nanocrystalline-Si/SiO_2 superlattice. Optics Express, 2011, 19, 2729.	3.4	17

#	Article	IF	CITATIONS
109	Optical-reconfigurable carbon nanotube and indium-tin-oxide complementary thin-film transistor logic gates. Nanoscale, 2018, 10, 13122-13129.	5.6	17
110	Uncovering the Indium Filament Revolution in Transparent Bipolar ITO/SiO _{<i>x</i>} /ITO Resistive Switching Memories. ACS Applied Materials & Interfaces, 2020, 12, 4579-4585.	8.0	17
111	Quantized STDP-based online-learning spiking neural network. Neural Computing and Applications, 2021, 33, 12317-12332.	5.6	17
112	Silicon nanocrystal-based non-volatile memory devices. Thin Solid Films, 2006, 504, 25-27.	1.8	16
113	Evolution of electroluminescence from multiple Si-implanted silicon nitride films with thermal annealing. Journal of Applied Physics, 2009, 105, 123101.	2.5	16
114	High temperature excitonic lasing characteristics of randomly assembled SnO2 nanowires. Applied Physics Letters, 2009, 95, .	3.3	16
115	Flexible Write-Once–Read-Many-Times Memory Device Based on a Nickel Oxide Thin Film. IEEE Transactions on Electron Devices, 2012, 59, 858-862.	3.0	16
116	HfO _x -Based RRAM Device With Sandwich-Like Electrode for Thermal Budget Requirement. IEEE Transactions on Electron Devices, 2020, 67, 4193-4200.	3.0	16
117	Defect-induced photoluminescence from tetraethylorthosilicate thin films containing mechanically milled silicon nanocrystals. Journal of Applied Physics, 2005, 97, 104307.	2.5	15
118	Distinguishing the effect of crystal-field screening from the effect of valence recharging on the 2p3/2 and 3d5/2 level energies of nanostructured copper. Applied Surface Science, 2006, 252, 2101-2107.	6.1	15
119	Charge trapping and retention behaviors of Ge nanocrystals distributed in the gate oxide near the gate synthesized by low-energy ion implantation. Journal of Applied Physics, 2007, 101, 124313.	2.5	15
120	Bandgap expansion and dielectric suppression of self-assembled Ge nanocrystals. Journal of Applied Physics, 2011, 109, .	2.5	15
121	Resistive Switching Behavior of Partially Anodized Aluminum Thin Film at Elevated Temperatures. IEEE Transactions on Electron Devices, 2012, 59, 2363-2367.	3.0	15
122	Winner-takes-all mechanism realized by memristive neural network. Applied Physics Letters, 2019, 115, .	3.3	15
123	Reverse l–V characteristics of Au/semi-insulating GaAs(1 0 0). Solid State Communications, 1997, 101, 715-720.	1.9	14
124	Charging mechanism in a SiO2 matrix embedded with Si nanocrystals. Journal of Applied Physics, 2006, 100, 096111.	2.5	14
125	A quantitative modeling of the contributions of localized surface plasmon resonance and interband transitions to absorbance of gold nanoparticles. Journal of Nanoparticle Research, 2012, 14, 1.	1.9	14
126	Development of optically transparent ZnS/poly(vinylpyrrolidone) nanocomposite films with high refractive indices and high Abbe numbers. Journal of Applied Polymer Science, 2013, 129, 1793-1798.	2.6	14

#	Article	IF	CITATIONS
127	Design of an electronic synapse with spike time dependent plasticity based on resistive memory device. Journal of Applied Physics, 2013, 113, .	2.5	14
128	Study of electrochromic characteristics in the near-infrared region of electrochromic devices based on solution-processed amorphous WO3 films. Materials Science in Semiconductor Processing, 2018, 88, 73-78.	4.0	14
129	Influence of Si nanocrystal distributed in the gate oxide on the MOS capacitance. IEEE Transactions on Electron Devices, 2006, 53, 730-736.	3.0	13
130	Charging effect of Al2O3 thin films containing Al nanocrystals. Applied Physics Letters, 2008, 93, 142106.	3.3	13
131	Ultraviolet Random Lasing Action from Highly Disordered n-AlN/p-GaN Heterojunction. ACS Applied Materials & Interfaces, 2011, 3, 1726-1730.	8.0	13
132	Controlled electroluminescence of n-ZnMgO/p-GaN light-emitting diodes. Applied Physics Letters, 2012, 101, .	3.3	13
133	Strong green emission in ZnO films after H2surface treatment. Journal Physics D: Applied Physics, 2012, 45, 185102.	2.8	13
134	Magnetron Sputtered <scp><scp>Ni</scp><fscp>â€rich Nickel Oxide Nanoâ€Films for Resistive Switching Memory Applications. International Journal of Applied Ceramic Technology, 2013, 10, 20-25.</fscp></scp>	2.1	13
135	Realization of write-once-read-many-times memory device with O ₂ plasma-treated indium gallium zinc oxide thin film. Applied Physics Letters, 2014, 104, 033505.	3.3	13
136	γ-Ray Radiation Effects on an HfO ₂ -Based Resistive Memory Device. IEEE Nanotechnology Magazine, 2018, 17, 61-64.	2.0	13
137	Effect of Surface Scattering of Electrons on Ratios of Optical Absorption and Scattering to Extinction of Gold Nanoshell. Nanoscale Research Letters, 2018, 13, 299.	5.7	13
138	A photovoltaic study of current transport and its influence on the determination of the Schottky barrier height in Schottky diodes. Semiconductor Science and Technology, 1993, 8, 2085-2091.	2.0	12
139	The effect of the temperature dependence of the ideality factor on metal-semiconductor solar devices. Semiconductor Science and Technology, 1993, 8, 1357-1360.	2.0	12
140	Influence of Nitrogen Proximity from the Si/SiO2 Interface on Negative Bias Temperature Instability. Japanese Journal of Applied Physics, 2002, 41, L1031-L1033.	1.5	12
141	Depth Profiling of Charging Effect of Si Nanocrystals Embedded in SiO2:Â A Study of Charge Diffusion among Si Nanocrystals. Journal of Physical Chemistry B, 2006, 110, 16499-16502.	2.6	12
142	Dependence of barrier height and effective mass on nitrogen concentration at SiOxNy/Si interface and gate oxide thickness. Smart Materials and Structures, 2006, 15, S39-S42.	3.5	12
143	Evolution of Photoluminescence Mechanisms of Si ⁺ -Implanted SiO ₂ Films with Thermal Annealing. Journal of Nanoscience and Nanotechnology, 2008, 8, 3555-3560.	0.9	12
144	Two-Terminal Write-Once-Read-Many-Times Memory Device Based on Charging-Controlled Current Modulation in Al/Al-Rich \$hbox{Al}_{2}hbox{O}_{3}\$/p-Si Diode. IEEE Transactions on Electron Devices, 2011, 58, 960-965.	3.0	12

#	Article	IF	CITATIONS
145	Influence of implantation dose on electroluminescence fromÂSi-implanted silicon nitride thin films. Applied Physics A: Materials Science and Processing, 2011, 104, 239-245.	2.3	12
146	A MoS ₂ -based coplanar neuron transistor for logic applications. Nanotechnology, 2017, 28, 214001.	2.6	12
147	Thickness effect of nickel oxide thin films on associated solution-processed write-once-read-many-times memory devices. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	12
148	Investigation of Schottky barrier formation for transition metal overlayers on InP and GaP(110) surfaces. Surface Science, 1992, 269-270, 979-987.	1.9	11
149	Snapback behaviour and its similarity to the switching behaviour in ultra-thin silicon dioxide films after hard breakdown. Journal Physics D: Applied Physics, 2001, 34, L95-L98.	2.8	11
150	Electroluminescence from n-In_2O_3:Sn randomly assembled nanorods/p-SiC heterojunction. Optics Express, 2010, 18, 15585.	3.4	11
151	Temperature-Dependent Charge Transport in Al/Al Nanocrystal Embedded Al2O3 Nanocomposite/p-Si Diodes. ECS Solid State Letters, 2012, 1, Q4-Q7.	1.4	11
152	Thickness Dependence of Optical Properties of Amorphous Indium Gallium Zinc Oxide Thin Films: Effects of Free-Electrons and Quantum Confinement. ECS Solid State Letters, 2015, 4, P29-P32.	1.4	11
153	Study of Multilevel High-Resistance States in HfO _{<italic>x</italic>} -Based Resistive Switching Random Access Memory by Impedance Spectroscopy. IEEE Transactions on Electron Devices, 2015, 62, 2684-2688.	3.0	11
154	Resonant scattering of green light enabled by Ag@TiO ₂ and its application in a green light projection screen. Nanoscale, 2018, 10, 2438-2446.	5.6	11
155	Study of Recall Time of Associative Memory in a Memristive Hopfield Neural Network. IEEE Access, 2019, 7, 58876-58882.	4.2	11
156	Toward transparent projection display: recent progress in frequency-selective scattering of RGB light based on metallic nanoparticle's localized surface plasmon resonance. Opto-Electronic Advances, 2019, 2, 19002001-19002015.	13.3	11
157	Post-stress interface trap generation induced by oxide-field stress with FN injection. IEEE Transactions on Electron Devices, 1998, 45, 1972-1977.	3.0	10
158	On the switching behaviour of post-breakdown conduction in ultra-thin SiO2films. Semiconductor Science and Technology, 2001, 16, 793-797.	2.0	10
159	Charging/discharging of silicon nanocrystals embedded in an SiO2matrix inducing reduction/recovery in the total capacitance and tunneling current. Smart Materials and Structures, 2006, 15, S43-S46.	3.5	10
160	Photon-induced conduction modulation in SiO2 thin films embedded with Ge nanocrystals. Applied Physics Letters, 2007, 90, 103102.	3.3	10
161	Tunable Surface Plasmon Resonance of Gold Nanoparticles Self-Assembled on Fused Silica Substrate. Electrochemical and Solid-State Letters, 2010, 13, K96.	2.2	10
162	The charge trapping and memory effect in SiO ₂ thin films containing Ge nanocrystals. Journal Physics D: Applied Physics, 2010, 43, 015102.	2.8	10

#	Article	IF	CITATIONS
163	Recovery from ultraviolet-induced threshold voltage shift in indium gallium zinc oxide thin film transistors by positive gate bias. Applied Physics Letters, 2013, 103, .	3.3	10
164	Realization of a Power-Efficient Transmitter Based on Integrated Artificial Neural Network. IEEE Access, 2018, 6, 68773-68781.	4.2	10
165	Application of Deep Compression Technique in Spiking Neural Network Chip. IEEE Transactions on Biomedical Circuits and Systems, 2020, 14, 274-282.	4.0	10
166	Study of negative-bias temperature-instability-induced defects using first-principle approach. Applied Physics Letters, 2003, 83, 3063-3065.	3.3	9
167	Profile of optical constants of SiO2 thin films containing Si nanocrystals. Journal of Applied Physics, 2004, 95, 8481-8483.	2.5	9
168	Electrical characteristics of Si nanocrystal distributed in a narrow layer in the gate oxide near the gate synthesized with very-low-energy ion beams. Journal of Applied Physics, 2006, 99, 106105.	2.5	9
169	Influence of thermal annealing on charge storage behaviour of Ge nanoclusters synthesized with low-energy Ge ion implantation. Journal Physics D: Applied Physics, 2009, 42, 035109.	2.8	9
170	Optical Transmission and Photoluminescence of Silicon Nitride Thin Films Implanted with Si Ions. Electrochemical and Solid-State Letters, 2009, 12, H38.	2.2	9
171	Self-learning ability realized with a resistive switching device based on a Ni-rich nickel oxide thin film. Applied Physics A: Materials Science and Processing, 2011, 105, 855-860.	2.3	9
172	Dielectric engineering of Ge nanocrystal/SiO2 nanocomposite thin films with Ge ion implantation: Modeling and measurement. Materials and Design, 2015, 83, 713-718.	7.0	9
173	Design of a High Performance Selective Solar Absorber with the Structure of SiO2-TiO2-TiNxOy-Cu. ECS Journal of Solid State Science and Technology, 2016, 5, N43-N47.	1.8	9
174	Theoretical study of leakage current effect on surface photovoltage induced by photoemission. Solid State Communications, 1992, 84, 815-818.	1.9	8
175	Reverse I-V characteristics of Au/semi-insulating InP (100). Semiconductor Science and Technology, 1993, 8, 709-711.	2.0	8
176	Determination of substrate doping, substrate carrier lifetime and density of surface recombination centres of MOSFETs by gate-controlled-diode measurements. Semiconductor Science and Technology, 1996, 11, 672-678.	2.0	8
177	Modulation of Capacitance Magnitude by Charging/Discharging in Silicon Nanocrystals Distributed Throughout the Gate Oxide in MOS Structures. Electrochemical and Solid-State Letters, 2005, 8, G8.	2.2	8
178	Influence of Si-nanocrystal distribution in the oxide on the charging behavior of MOS structures. IEEE Transactions on Electron Devices, 2006, 53, 914-917.	3.0	8
179	Relationship Between Current Transport and Electroluminescence in \$hbox{Si}^{+}\$-Implanted \$ hbox{SiO}_{2}\$ Thin Films. IEEE Transactions on Electron Devices, 2009, 56, 2785-2791.	3.0	8
180	Charging effect and capacitance modulation of Ni-rich NiO thin film. Applied Physics Letters, 2009, 95, 012104.	3.3	8

#	Article	IF	CITATIONS
181	Magnetron Sputtered nc-Al/ <i>α</i> -Al ₂ O ₃ Nanocomposite Thin Films for Nonvolatile Memory Application. Journal of Nanoscience and Nanotechnology, 2009, 9, 4116-4120.	0.9	8
182	InGaZnO Thin-Film Transistors With Coplanar Control Gates for Single-Device Logic Applications. IEEE Transactions on Electron Devices, 2016, 63, 1383-1387.	3.0	8
183	An energy-efficient deep convolutional neural networks coprocessor for multi-object detection. Microelectronics Journal, 2020, 98, 104737.	2.0	8
184	Transparent electronic and photoelectric synaptic transistors based on the combination of an InGaZnO channel and a TaO _{<i>x</i>} gate dielectric. Nanoscale, 2022, 14, 10245-10254.	5.6	8
185	Depth Profiling of Si Oxidation States in Si-Implanted SiO2Films by X-Ray Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 2003, 42, L1394-L1396.	1.5	7
186	Dynamic NBTI lifetime model for inverter-like waveform. Microelectronics Reliability, 2005, 45, 1115-1118.	1.7	7
187	Characteristics of mechanically milled silicon nanocrystals embedded in TEOS thin films. Journal of Crystal Growth, 2006, 288, 92-95.	1.5	7
188	Current conduction in Al/Si nanocrystal embedded SiO2/p-Si diodes with various distributions of Si nanocrystals in the oxide. Journal of Applied Physics, 2009, 106, 013718.	2.5	7
189	Quenching and Reactivation of Electroluminescence by Charge Trapping and Detrapping in Si-Implanted Silicon Nitride Thin Film. IEEE Transactions on Electron Devices, 2009, 56, 3212-3217.	3.0	7
190	Size-suppressed dielectrics of Ge nanocrystals: skin-deep quantum entrapment. Nanoscale, 2012, 4, 1308.	5.6	7
191	Wavelength tunable electroluminescence from randomly assembled n-CdS _x Se _{1â^'x} nanowires/p ⁺ -SiC heterojunction. Nanoscale, 2012, 4, 1467-1470.	5.6	7
192	Effect of Heat Diffusion During State Transitions in Resistive Switching Memory Device Based on Nickel-Rich Nickel Oxide Film. IEEE Transactions on Electron Devices, 2012, 59, 1558-1562.	3.0	7
193	Influences of water molecules on the electronic properties of atomically thin molybdenum disulfide. Applied Physics Letters, 2017, 111, .	3.3	7
194	Design of a Neural Network-Based VCO With High Linearity and Wide Tuning Range. IEEE Access, 2019, 7, 60120-60125.	4.2	7
195	Spikeâ€driven gated recurrent neural network processor for electrocardiogram arrhythmias detection realised in 55â€nm CMOS technology. Electronics Letters, 2020, 56, 1230-1232.	1.0	7
196	A study of recombination current in Schottky contacts by photovoltage measurements. Semiconductor Science and Technology, 1994, 9, 2101-2106.	2.0	6
197	Optical transitions in germanium dioxide. Thin Solid Films, 1996, 283, 230-234.	1.8	6
198	A novel approach to quantitative determination of charge trapping near channel/drain edge in MOSFETs. Solid-State Electronics, 2002, 46, 2013-2016.	1.4	6

#	Article	IF	CITATIONS
199	Charging effect of Si nanocrystals in gate oxide near gate on MOS capacitance. Electronics Letters, 2003, 39, 1164.	1.0	6
200	Random capacitance modulation due to charging/discharging in Si nanocrystals embedded in gate dielectric. Nanotechnology, 2005, 16, 1119-1122.	2.6	6
201	A study of the influence of tunnel oxide thickness on the performance of flash memory based on ion-beam synthesized silicon nanocrystals. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1291-1295.	1.8	6
202	Dielectric functions of SiO2 film embedded with silicon nanocrystals. Journal of Crystal Growth, 2006, 288, 87-91.	1.5	6
203	A Simple Negative Bias Temperature Instability Characterization Methodology to Minimize the Immediate Recovery Effect during Measurement. Japanese Journal of Applied Physics, 2006, 45, 6137-6140.	1.5	6
204	Light-induced instability in current conduction of aluminum nitride thin films embedded with Al nanocrystals. Applied Physics Letters, 2008, 92, 013102.	3.3	6
205	Formation of uniform nanoscale oxide layers assembled by overlapping oxide lines using atomic force microscopy. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2009, 8, 043050.	0.9	6
206	Charging Effect of Aluminum Nitride Thin Films Containing Al Nanocrystals. Journal of Nanoscience and Nanotechnology, 2010, 10, 599-603.	0.9	6
207	Collective Excitations and Dielectric Function of Self-Assembled Gold Nanoparticles on a Silicon Substrate. Electrochemical and Solid-State Letters, 2010, 13, K39.	2.2	6
208	Static dielectric constant of Al nanocrystal/Al2O3 nanocomposite thin films determined by the capacitance-voltage reconstruction technique. Applied Physics Letters, 2010, 96, 173110.	3.3	6
209	Optical Properties of Gold Nanoparticles on Heavily-Doped Si Substrate Synthesized with an Electrochemical Process. Journal of the Electrochemical Society, 2011, 158, K152.	2.9	6
210	Evolution of the localized surface plasmon resonance and electron confinement effect with the film thickness in ultrathin Au films. Journal of Nanoparticle Research, 2015, 17, 1.	1.9	6
211	W/Cu thin film infrared reflector for TiNxOy based selective solar absorber with high thermal stability. Journal of Applied Physics, 2017, 121, .	2.5	6
212	Design of AM Self-Capacitive Transparent Touch Panel Based on a-IGZO Thin-Film Transistors. IEEE Access, 2020, 8, 76929-76934.	4.2	6
213	A calculation of the photovoltage at the metal-semiconductor interface. Surface Science, 1993, 294, 367-372.	1.9	5
214	Interfacial Fermi level and surface band bending in Ni/semiâ€insulating GaAs contact. Journal of Applied Physics, 1995, 78, 4796-4798.	2.5	5
215	Post-Breakdown Conduction Instability of Ultrathin SiO2Films Observed in Ramped-Current and Ramped-Voltage Current–Voltage Measurements. Japanese Journal of Applied Physics, 2002, 41, 3047-3051.	1.5	5
216	Gate oxide thickness dependence of edge charge trapping in nmos transistors caused by charge injection under constant-current stress. IEEE Transactions on Electron Devices, 2003, 50, 1548-1550.	3.0	5

#	Article	IF	CITATIONS
217	Modeling and Characterization of Nitrogen-Enhanced Negative-Bias Temperature Instability in p-Channel MOSFETs. Journal of the Electrochemical Society, 2007, 154, G255.	2.9	5
218	Direct Writing of Spot and Line Bonds for Microsystem Packaging Using Transmission Laser Bonding Technique. Materials and Manufacturing Processes, 2007, 22, 71-80.	4.7	5
219	Implant Energy-Dependent Enhancement of Electroluminescence from Ge-Implanted SiO[sub 2] Thin Films. Electrochemical and Solid-State Letters, 2009, 12, H238.	2.2	5
220	Charge Storage Behaviors of Ge Nanocrystals Embedded in SiO ₂ for the Application in Non-Volatile Memory Devices. Journal of Nanoscience and Nanotechnology, 2010, 10, 4517-4521.	0.9	5
221	Improvement of Negative Bias Temperature Instability by Stress Proximity Technique. IEEE Transactions on Electron Devices, 2010, 57, 238-243.	3.0	5
222	Resistive Switching in p-Type Nickel Oxide/n-Type Indium Gallium Zinc Oxide Thin Film Heterojunction Structure. ECS Journal of Solid State Science and Technology, 2016, 5, Q239-Q243.	1.8	5
223	Synthesis of IGZO ink and study of ink-jet printed IGZO thin films with different Ga concentrations. Solid-State Electronics, 2017, 138, 108-112.	1.4	5
224	Investigation of Electrical Noise Signal Triggered Resistive Switching and Its Implications. IEEE Transactions on Electron Devices, 2020, 67, 4178-4184.	3.0	5
225	Performance Enhancement of Transparent Amorphous IGZO Thin-Film Transistor Realized by Sputtered Amorphous AlOx Passivation Layer. ECS Journal of Solid State Science and Technology, 2021, 10, 045006.	1.8	5
226	Determination of leakage resistance of Schottky contacts by photovoltage measurements. Journal of Applied Physics, 1994, 75, 7361-7364.	2.5	4
227	Influence of annealing on Fermiâ€level pinning and current transport at Auâ€Si and Auâ€GaAs Interfaces. Journal of Applied Physics, 1995, 77, 6724-6726.	2.5	4
228	Reproducibility of transmission line measurement of bipolar I-V characteristics of MOSFETs. IEEE Transactions on Instrumentation and Measurement, 1999, 48, 721-723.	4.7	4
229	Influence of interfacial nitrogen on edge charge trapping at the interface of gate oxide/drain extension in metal–oxide–semiconductor transistors. Applied Physics Letters, 2003, 82, 3113-3115.	3.3	4
230	A new waveform-dependent lifetime model for dynamic NBTI in PMOS transistor. , 0, , .		4
231	Dielectric functions of densely stacked Si nanocrystal layer embedded in SiO2 thin films. Applied Physics Letters, 2006, 89, 251910.	3.3	4
232	Si ion-induced instability in flatband Voltage of Si/sup +/-implanted gate oxides. IEEE Transactions on Electron Devices, 2006, 53, 1280-1282.	3.0	4
233	Room-Temperature Visible Electroluminescence From Aluminum Nitride Thin Film Embedded With Aluminum Nanocrystals. IEEE Transactions on Electron Devices, 2008, 55, 3605-3609.	3.0	4
234	Anomalous capacitance-voltage characteristics of Al/Al-rich Al2O3/p-Si capacitors and their reconstruction. Applied Physics Letters, 2009, 94, 243106.	3.3	4

#	Article	IF	CITATIONS
235	Design of a Near-Perfect Anti Reflective Layer for Si Photodetectors Based on a SiO2Film Embedded with Si Nanocrystals. Japanese Journal of Applied Physics, 2009, 48, 060206.	1.5	4
236	Profile Uniformity of Overlapped Oxide Dots Induced by Atomic Force Microscopy. Journal of Nanoscience and Nanotechnology, 2010, 10, 4390-4399.	0.9	4
237	A Two-Terminal Write-Once-Read-Many-Times-Memory Device Based on an Aluminum Nitride Thin Film Containing Al Nanocrystals. Journal of Nanoscience and Nanotechnology, 2010, 10, 5796-5799.	0.9	4
238	Comparison of Charge Storage Behavior of Electrons and Holes in a Continuous Ge Nanocrystal Layer. Nanoscience and Nanotechnology Letters, 2010, 2, 7-10.	0.4	4
239	Competition of Resistive-Switching Mechanisms in Nickel-Rich Nickel Oxide Thin Films. Electrochemical and Solid-State Letters, 2011, 14, H400.	2.2	4
240	Uniform and electroforming-free resistive memory devices based on solution-processed triple-layered NiO/Al2O3 thin films. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	2.3	4
241	Implementation of a Low Noise Amplifier With Self-Recovery Capability. IEEE Access, 2019, 7, 43076-43083.	4.2	4
242	Efficient and reconfigurable reservoir computing to realize alphabet pronunciation recognition based on processing-in-memory. Applied Physics Letters, 2021, 119, .	3.3	4
243	Flexible Nanoscale Memory Device Based on Resistive Switching in Nickel Oxide Thin Film. Nanoscience and Nanotechnology Letters, 2012, 4, 940-943.	0.4	4
244	Sharp selective scattering of red, green, and blue light achieved via gain material's loss compensation. Optics Express, 2019, 27, 9189.	3.4	4
245	Frequency-controlled low-level current source based on charge pumping. Electronics Letters, 2001, 37, 1046.	1.0	4
246	Characterization of Ptâ€ s i interface by spectroscopic ellipsometry. Journal of Applied Physics, 1994, 76, 7423-7427.	2.5	3
247	Improvements in the PSB AC-DC transfer capabilities and a proposal for range extension. , 0, , .		3
248	Suppression of Nitridation-Induced Interface Traps and Hole Mobility Degradation by Nitrogen Plasma Nitridation. Electrochemical and Solid-State Letters, 2002, 5, G26.	2.2	3
249	A quantitative study of the relationship between the oxide charge trapping over the drain extension and the off-state drain leakage current. Applied Physics Letters, 2004, 85, 4211-4213.	3.3	3
250	A novel empirical model for NBTI recovery with the modulated measurement time frame. , 2006, , .		3
251	Influences of interface oxidation on transmission laser bonding of wafers for microsystem packaging. Microsystem Technologies, 2006, 13, 49-59.	2.0	3
252	Charge trapping phenomena of tetraethylorthosilicate thin film containing Si nanocrystals synthesized by solid-state reaction. Nanotechnology, 2006, 17, 4078-4081.	2.6	3

#	Article	IF	CITATIONS
253	Measurement of Dispersion Stability of Surface-Modified Nanosized Carbon Black in Various Liquids. Journal of Nanoscience and Nanotechnology, 2007, 7, 3827-3829.	0.9	3
254	Influence of excess Si distribution in the gate oxide on the memory characteristics of MOSFETs. Applied Physics A: Materials Science and Processing, 2008, 91, 411-413.	2.3	3
255	A Simple Route to Growth of Silicon Nanowires. Journal of Nanoscience and Nanotechnology, 2008, 8, 5787-5790.	0.9	3
256	Influence of hydrogen dispersive diffusion in nitrided gate oxide on negative bias temperature instability. Applied Physics Letters, 2008, 93, 013501.	3.3	3
257	Annealing-Induced Changes in Electrical Characteristics of Al/Al-Rich \$hbox{Al}_{2}hbox{O}_{3}/phbox{-Si}\$ Diodes. IEEE Transactions on Electron Devices, 2011, 58, 33-38.	3.0	3
258	Temperature dependence of current transport in Al/Al2O3 nanocomposite thin films. Journal of Applied Physics, 2011, 110, 096108.	2.5	3
259	Realization of transient memory-loss with NiO-based resistive switching device. Applied Physics A: Materials Science and Processing, 2012, 109, 349-352.	2.3	3
260	Si nanocrystal-based triple-layer anti-reflection coating for Si solar cells. Journal of Applied Physics, 2013, 114, 053109.	2.5	3
261	Modeling the Post-Breakdown I-V Characteristics of Ultrathin SiO2 Films with Multiple Snapbacks. Japanese Journal of Applied Physics, 2001, 40, L666-L668.	1.5	3
262	Temperature Dependence of Resistive Switching in Aluminum/Anodized Aluminum Film Structure. Nanoscience and Nanotechnology Letters, 2011, 3, 222-225.	0.4	3
263	Epilepsy detection with artificial neural network based on as-fabricated neuromorphic chip platform. AIP Advances, 2022, 12, 035106.	1.3	3
264	Numerical study of electrostatic properties of metal/semi-insulating GaAs contacts. Solid State Communications, 1995, 94, 287-291.	1.9	2
265	Fermi level position at metal/semi-insulating-GaAs (1 0 0) interfaces studied by photoelectric techniques. Solid State Communications, 1997, 102, 833-836.	1.9	2
266	Electrically induced room temperature metastability in semi-insulating GaAs. Solid State Communications, 1998, 108, 907-911.	1.9	2
267	Power-Law Dependence of Charge Trapping on Injected Charge in Very Thin SiO2 Films. Japanese Journal of Applied Physics, 2002, 41, L384-L386.	1.5	2
268	Barrier Height Change in Very Thin SiO[sub 2] Films Caused by Charge Injection. Electrochemical and Solid-State Letters, 2002, 5, G96.	2.2	2
269	Negative-bias-temperature-instability (NBTI) for p/sup +/-gate pMOSFET with ultra-thin plasma-nitrided gate dielectrics. , 0, , .		2
270	Characterization of interface degradation in deep submicron MOSFETs by gate-controlled-diode measurement. Microelectronics Journal, 2002, 33, 639-643.	2.0	2

#	Article	IF	CITATIONS
271	An approach to optical-property profiling of a planar-waveguide structure of Si nanocrystals embedded in SiO2. Nanotechnology, 2005, 16, 2657-2660.	2.6	2
272	Modeling and Characterization of Negative Bias Temperature Instability in p-Channel MOSFETs. ECS Transactions, 2007, 6, 283-299.	0.5	2
273	Conduction switching in aluminum nitride thin films containing Al nanocrystals. Applied Physics A: Materials Science and Processing, 2008, 93, 483-487.	2.3	2
274	Charging effect on electroluminescence performance of nc-Si/a-SiO2 films. Journal of Applied Physics, 2010, 107, 043709.	2.5	2
275	Influence of SiO2 Layer on the Dielectric Function of Gold Nanoparticles on Si Substrate. Electrochemical and Solid-State Letters, 2012, 15, K5.	2.2	2
276	Electroluminescence from SiO2 Thin Film Embedded with Self-Assembled Gold Nanoparticles. Nanoscience and Nanotechnology Letters, 2013, 5, 857-860.	0.4	2
277	Selective Scattering of Blue and Red Light Based on Silver and Gold Nanocubes. ECS Journal of Solid State Science and Technology, 2019, 8, R51-R57.	1.8	2
278	3D Geometric Engineering of the Double Wedge-Like Electrodes for Filament-Type RRAM Device Performance Improvement. IEEE Access, 2020, 8, 4924-4934.	4.2	2
279	Al Content–Dependent Resistive Switching in Al-Rich AlO _x N _y Thin Films. Nanoscience and Nanotechnology Letters, 2014, 6, 835-839.	0.4	2
280	Numerical study of the decay of photovoltage at metal-semiconductor interfaces. Solid State Communications, 1993, 87, 1163-1167.	1.9	1
281	Leakage current induced drop in Ef in pes studies of Schottky barrier formation. Solid State Communications, 1994, 89, 779-781.	1.9	1
282	Cathodoluminescence from interband transitions in germanium (111) and gallium arsenide (100) crystals. Physical Review B, 1995, 52, 1452-1455.	3.2	1
283	Influence of voltage contacts on precision measurements of the quantized Hall resistance: an effect of externally injected current. IEEE Transactions on Instrumentation and Measurement, 1998, 47, 592-594.	4.7	1
284	Influence of trapped charges on low-level leakage current in thin silicon dioxide films. , 0, , .		1
285	Influence of nitrogen concentration in nitrided oxides on interface trap generation caused by Fowler-Nordheim injection. Journal Physics D: Applied Physics, 2002, 35, L115-L117.	2.8	1
286	Characterization of ultrathin plasma nitrided gate dielectrics in pMOSFET for 0.18 μm technology and beyond. , 0, , .		1
287	Influences of nitridation on tunneling barrier change and charge trapping caused by electrical stress. Journal of Applied Physics, 2003, 93, 3114-3116.	2.5	1
288	Impact of Nonuniform Graded Dopant Profile in Polysilicon Gate on Gate Leakage Current. IEEE Transactions on Electron Devices, 2005, 52, 1200-1204.	3.0	1

#	Article	IF	CITATIONS
289	Energy Shifts of Si Oxidation States in the System of Si Nanocrystals Embedded in SiO ₂ Matrix. Journal of Nanoscience and Nanotechnology, 2007, 7, 2506-2510.	0.9	1
290	Parasitic memory effect induced by high erasing pulses in metal-oxide-semiconductor field-effect transistor device containing silicon nanocrystals. Journal of Applied Physics, 2009, 105, 114501.	2.5	1
291	Capacitance switching in SiO2 thin film embedded with Ge nanocrystals caused by ultraviolet illumination. Applied Physics Letters, 2009, 95, 091111.	3.3	1
292	Charge Storage Mechanism of Si Nanocrystals Embedded SiO ₂ Films. Nanoscience and Nanotechnology Letters, 2009, 1, 176-181.	0.4	1
293	CMOS-compatible light-emitting devices based on thin aluminum nitride film containing Al nanocrystals. Applied Physics A: Materials Science and Processing, 2009, 95, 753-756.	2.3	1
294	Charging influence on current conduction in NiO thin film embedded with Ni nanocrystals. Journal Physics D: Applied Physics, 2009, 42, 225104.	2.8	1
295	Physics of electron mobility independent of channel orientation in n-channel transistors based on (100) silicon wafers and its experimental verification. Applied Physics Letters, 2010, 97, 133508.	3.3	1
296	Charging Effect on Conductance of Magnetron Sputtered Si Nanocrystals Embedded SiO ₂ Films. Nanoscience and Nanotechnology Letters, 2010, 2, 226-230.	0.4	1
297	Ink-jet printed In-Ga-Zn oxide nonvolatile TFT memory utilizing silicon nanocrystals embedded in SiO <inf>2</inf> gate dielectric. , 2013, , .		1
298	An Experimental Study of Lateral Charge Transfer in Silicon Nanocrystal Layer Embedded in SiO ₂ Thin Film. Nanoscience and Nanotechnology Letters, 2014, 6, 798-804.	0.4	1
299	Lateral Conduction Switching in Sputtered Niâ€rich NiO Thin Films for Writeâ€Onceâ€Readâ€Manyâ€Times Memory Applications. International Journal of Applied Ceramic Technology, 2014, 11, 732-737.	2.1	1
300	Resistive switching characteristics of RRAM devices based on spin-coated a-IGZO thin films and ink-jet printed Ag electrodes. , 2016, , .		1
301	Nanoparticle-assisted Frenkel–Poole emission in two-terminal charging-controlled memory devices based on Si-rich silicon nitride thin films. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	1
302	Resistive Switching in a Ni-Rich Nickel Oxide Thin Film. Nanoscience and Nanotechnology Letters, 2011, 3, 267-271.	0.4	1
303	A Large-Size HfO2 Based RRAM Structure Suitable for Integration of One RRAM with One InGaZnO Thin Film Transistor for Large-Area Applications. ECS Journal of Solid State Science and Technology, 2021, 10, 115004.	1.8	1
304	Numerical modeling of transient characteristics of photovoltage in Schottky contacts. Journal of Applied Physics, 1994, 76, 7624-7626.	2.5	0
305	Optical Properties of Interband Transitions in the Oxygenâ€Plasmaâ€Anodised Film on Gallium Arsenide ã€^100〉. Physica Status Solidi (B): Basic Research, 1995, 192, 217-222.	1.5	0
306	Instabilities in gate-controlled-diode characteristics of n-MOSFETs following hot-carrier injection. Semiconductor Science and Technology, 1997, 12, 1365-1368.	2.0	0

#	Article	IF	CITATIONS
307	Instability in post-breakdown conduction in ultra-thin gate oxide. , 0, , .		Ο
308	Study of edge charge trapping in gate oxide caused by FN and hot-carrier injection. , 0, , .		0
309	Influences of Nitridation on Barrier Height Change Caused by Electrical Stress. Japanese Journal of Applied Physics, 2002, 41, L1425-L1427.	1.5	0
310	Study of influence of nitrogen concentration in nitrided oxide on interface trap generation. , 0, , .		0
311	Effects of post-decoupled-plasma-nitridation annealing of ultra-thin gate oxide. , 0, , .		Ο
312	Photoluminescence of Si Nanosolids Near the Lower End of the Size Limit ChemInform, 2003, 34, no.	0.0	0
313	Real time evolution of charge decay characteristics in silicon nanocrystals. , 2004, , .		0
314	Dependence of barrier height and effective electron mass on gate oxide thickness and nitrogen concentration at SiO x N y /Si interface. , 2004, 5274, 493.		0
315	Evolutions and distributions of Si nanocrystals and other Si oxidation states in Si-implanted SiO2 films. , 2004, 5275, 374.		0
316	Optical properties and their depth profiling of Si nanocrystals embedded in SiO 2 matrix. , 2004, 5275, 378.		0
317	Charging/discharging induced premature breakdown/recovery in Si nanocrystals embedded in SiO 2 matrix. , 2004, 5275, 18.		Ο
318	Characterization of Si Nanocrystals Embedded in SiO ₂ with X-Ray Photoelectron Spectroscopy. Journal of Metastable and Nanocrystalline Materials, 2005, 23, 11-14.	0.1	0
319	Optical-Property Profiling of SiO ₂ Films Containing Si Nanocrystals Formed by Si ⁺ Implantation. Journal of Metastable and Nanocrystalline Materials, 2005, 23, 133-136.	0.1	0
320	DISSIPATION OF CHARGES IN SILICON NANOCRYSTALS EMBEDDED IN SiO2 DIELECTRIC FILMS: AN ELECTROSTATIC FORCE MICROSCOPY STUDY. International Journal of Nanoscience, 2005, 04, 709-715.	0.7	0
321	Synthesis, Characterization and Oxidation Effects of Solid-State Reaction Silicon Nanocrystals. , 2006, , \cdot		0
322	An electrical study of behaviors of Si nanocrystals distributed in the gate oxide near the oxide/substrate interface of a MOS structure. Thin Solid Films, 2006, 504, 32-35.	1.8	0
323	Simulation of Flash Memory Characteristics based on Discrete Nanoscale Silicon. , 2006, , .		0
324	CMOS-compatible light emission device based on thin aluminum nitride film containing Al		0

nanocrystals. , 2007, , .

#	ARTICLE	IF	CITATIONS
325	APPLICATION OF SILICON NANOCRYSTAL IN NON-VOLATILE MEMORY DEVICES. , 2007, , 419-472.		0
326	Charging effect in germanium nanocrystals embedded in a SiO2 matrix. , 2007, , .		0
327	A comparative study on the dielectric functions of isolated Si nanocrystals and densely stacked Si nanocrystal layer embedded in SiO 2 synthesized with Si ion implantation. , 2008, , .		0
328	Influence of nanocrystal distribution on electroluminescence from Si ⁺ -implanted SiO 2 thin films. Proceedings of SPIE, 2008, , .	0.8	0
329	Large magnetic moment obtained in Cu-doped ZnO nanoclusters. , 2009, , .		0
330	Si-Based Light-Emitting Structure Synthesized with Low-Energy Ion Implantation at a Low Dosage. Journal of Nanoscience and Nanotechnology, 2010, 10, 595-598.	0.9	0
331	New Structures and Materials for Next Generation Photonic Technology. Applied Mechanics and Materials, 0, 120, 556-560.	0.2	0
332	Profile Uniformity of Overlapped Oxide Dots Induced by Atomic Force Microscopy: (Journal of) Tj ETQq0 0 0 rgBT Nanotechnology, 2011, 11, 899-899.	/Overlock 0.9	10 Tf 50 46 0
333	Modeling of lateral charge transfer in Si nanocrystals in SiO2 thin film. Journal of Applied Physics, 2012, 111, 073707.	2.5	0
334	Low dimension structures and devices for new generation photonic technology. , 2014, , .		0
335	Influence of the Excess Al Content on Memory Behaviors of WORM Devices Based on Sputtered Al-Rich Aluminum Oxide Thin Films. Nanoscience and Nanotechnology Letters, 2014, 6, 845-848.	0.4	0
336	Tunable long-distance light transportation along Au nanoparticle chains: promising for optical interconnect. Journal of Nanoparticle Research, 2014, 16, 1.	1.9	0
337	Stock Price Prediction Based on an Energy-Efficient Spiking-LSTM Hardware Accelerator. Journal of Physics: Conference Series, 2021, 1828, 012050.	0.4	0
338	Design of a constant loop bandwidth phase-locked loop based on artificial neural network. IEICE Electronics Express, 2021, 18, 20210120-20210120.	0.8	0
339	<i>A Special Issue on</i> Nanoelectronics. Nanoscience and Nanotechnology Letters, 2014, 6, 727-728.	0.4	0
340	Electronic and Optical Properties of Si and Ge Nanocrystals. Advances in Materials Science and Engineering, 2016, , 215-254.	0.4	0
341	Light Emission Properties of Si Nanocrystals Embedded in a Dielectric Matrix. Advances in Materials Science and Engineering, 2016, , 255-282.	0.4	0